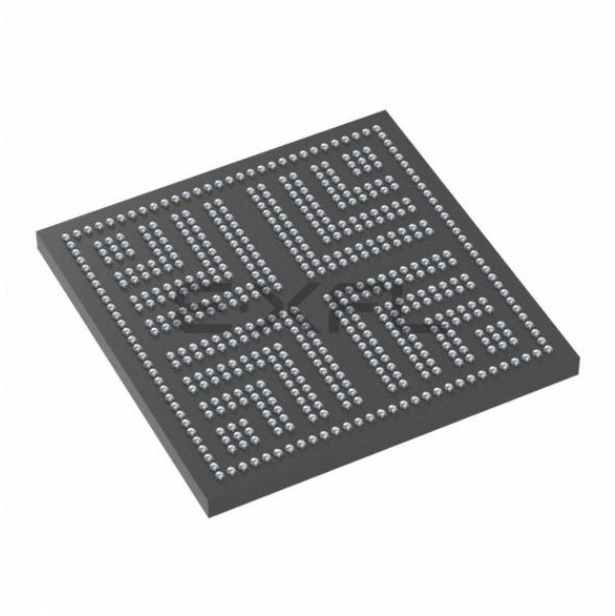
Microchip Technology - MPF200T-1FCSG536E Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	192000
Total RAM Bits	13619200
Number of I/O	300
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	536-LFBGA, CSPBGA
Supplier Device Package	536-CSPBGA (16x16)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf200t-1fcsg536e

The maximum overshoot duration is specified as a high-time percentage over the lifetime of the device. A DC signal is equivalent to 100% of the duty-cycle.

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for HSIO.

Table 6 • Maximum Overshoot During Transitions for HSIO

AC (V_{IN}) Overshoot Duration as % at T_J = 100 °C	Condition (V)
100	1.8
100	1.85
100	1.9
100	1.95
100	2
100	2.05
100	2.1
100	2.15
100	2.2
90	2.25
30	2.3
7.5	2.35
1.9	2.4

Note: Overshoot level is for VDDI at 1.8 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for HSIO.

Table 7 • Maximum Undershoot During Transitions for HSIO

AC (V_{IN}) Undershoot Duration as % at T_J = 100 °C	Condition (V)
100	–0.05
100	–0.1
100	–0.15
100	–0.2
100	–0.25
100	–0.3
100	–0.35
100	–0.4
44	–0.45
14	–0.5
4.8	–0.55
1.6	–0.6

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for GPIO.

Note: The following dedicated pins do not support hot socketing: TMS, TDI, TRSTB, DEVRST_N, and FF_EXIT_N. Weak pull-up (as specified in GPIO) is always enabled.

6.3 Input and Output

The following section describes:

- DC I/O levels
- Differential and complementary differential DC I/O levels
- HSIO and GPIO on-die termination specifications
- LVDS specifications

6.3.1 DC Input and Output Levels

The following tables list the DC I/O levels.

Table 12 • DC Input Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{IL} Min (V)	V_{IL} Max (V)	V_{IH} Min (V)	V_{IH}[1] Max (V)
PCI	3.15	3.3	3.45	–0.3	0.3 × V_{DDI}	0.5 × V_{DDI}	3.45
LVTTL	3.15	3.3	3.45	–0.3	0.8	2	3.45
LVCMOS33	3.15	3.3	3.45	–0.3	0.8	2	3.45
LVCMOS25	2.375	2.5	2.625	–0.3	0.7	1.7	2.625
LVCMOS18	1.71	1.8	1.89	–0.3	0.35 × V_{DDI}	0.65 × V_{DDI}	1.89
LVCMOS15	1.425	1.5	1.575	–0.3	0.35 × V_{DDI}	0.65 × V_{DDI}	1.575
LVCMOS12	1.14	1.2	1.26	–0.3	0.35 × V_{DDI}	0.65 × V_{DDI}	1.26
SSTL25I[2]	2.375	2.5	2.625	–0.3	V_{REF} – 0.15	V_{REF} + 0.15	2.625
SSTL25II[2]	2.375	2.5	2.625	–0.3	V_{REF} – 0.15	V_{REF} + 0.15	2.625
SSTL18I[2]	1.71	1.8	1.89	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	1.89
SSTL18II[2]	1.71	1.8	1.89	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	1.89
SSTL15I	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575
SSTL15II	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575

Table 13 • DC Output Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{OL} Min (V)	V_{OL} Max (V)	V_{OH} Min (V)	V_{OH} Max (V)	I_{OL}[2,6] mA	I_{OH}[2,6] mA
PCI[1]	3.15	3.3	3.45		0.1 × V_{DDI}	0.9 × V_{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVCMOS33	3.15	3.3	3.45		0.4	V_{DDI} – 0.4			
LVCMOS25	2.375	2.5	2.625		0.4	V_{DDI} – 0.4			
LVCMOS18	1.71	1.8	1.89		0.45	V_{DDI} – 0.45			
LVCMOS15	1.425	1.5	1.575		0.25 × V_{DDI}	0.75 × V_{DDI}			
LVCMOS12	1.14	1.2	1.26		0.25 × V_{DDI}	0.75 × V_{DDI}			
SSTL25I[3]	2.375	2.5	2.625		V_{TT} – 0.608	V_{TT} + 0.608		8.1	8.1
SSTL25II[3]	2.375	2.5	2.625		V_{TT} – 0.810	V_{TT} + 0.810		16.2	16.2
SSTL18I[3]	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603		6.7	6.7
SSTL18II[3]	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603		13.4	13.4
SSTL15I[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/40	(V_{DDI} – V_{OH}) /40
SSTL15II[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/34	(V_{DDI} – V_{OH}) /34
SSTL135I[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/40	(V_{DDI} – V_{OH}) /40
SSTL135II[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/34	(V_{DDI} – V_{OH}) /34
HSTL15I	1.425	1.5	1.575		0.4	V_{DDI} – 0.4		8	8
HSTL15II	1.425	1.5	1.575		0.4	V_{DDI} – 0.4		16	16

Min (%)	Typ	Max (%)	Unit	Condition
–20	60	20	Ω	V_{DDI} = 1.2 V
–20	120	20	Ω	V_{DDI} = 1.2 V

Note: Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI}. For 50 Ω/75 Ω/150 Ω cases, nearest supported values of 40 Ω/60 Ω/120 Ω are used.

Table 19 • Single-Ended Termination to VDDI (Internal Parallel Termination to VDDI)

Min (%)	Typ	Max (%)	Unit	Condition
–20	34	20	Ω	V_{DDI} = 1.2 V
–20	40	20	Ω	V_{DDI} = 1.2 V
–20	48	20	Ω	V_{DDI} = 1.2 V
–20	60	20	Ω	V_{DDI} = 1.2 V
–20	80	20	Ω	V_{DDI} = 1.2 V
–20	120	20	Ω	V_{DDI} = 1.2 V
–20	240	20	Ω	V_{DDI} = 1.2 V

Note: Measured at 80% of V_{DDI}.

Table 20 • Single-Ended Termination to VSS (Internal Parallel Termination to VSS)

Min (%)	Typ	Max (%)	Unit	Condition
–20	120	20	Ω	V_{DDI} = 1.8 V/1.5 V
–20	240	20	Ω	V_{DDI} = 1.8 V/1.5 V
–20	120	20	Ω	V_{DDI} = 1.2 V
–20	240	20	Ω	V_{DDI} = 1.2 V

Note: Measured at 50% of V_{DDI}.

6.3.5 GPIO On-Die Termination

The following table lists the on-die termination calibration accuracy specifications for GPIO bank.

Table 21 • On-Die Termination Calibration Accuracy Specifications for GPIO Bank

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Differential termination[1]	Internal differential termination	–20	100	20	Ω	V_{ICM} < 0.8 V
		–20	100	40	Ω	0.6 V < V_{ICM} < 1.65 V
		–20	100	80	Ω	1.4 V < V_{ICM}
Single-ended thevenin termination[2, 3]	Internal parallel thevenin termination	–40	50	20	Ω	V_{DDI} = 1.8 V/1.5 V
		–40	75	20	Ω	V_{DDI} = 1.8 V
		–40	150	20	Ω	V_{DDI} = 1.8 V
		–20	20	20	Ω	V_{DDI} = 1.5 V
		–20	30	20	Ω	V_{DDI} = 1.5 V
		–20	40	20	Ω	V_{DDI} = 1.5 V
		–20	60	20	Ω	V_{DDI} = 1.5 V
		–20	120	20	Ω	V_{DDI} = 1.5 V

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Single-ended termination to V_{SS}[4, 5]	Internal parallel termination to V_{SS}	–20	120	20	Ω	V_{DDI} = 2.5 V/1.8 V/1.5 V/1.2 V
		–20	240	20	Ω	V_{DDI} = 2.5 V/1.8 V/1.5 V/1.2 V

1. Measured across P to N with 400 mV bias.
2. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI}.
3. For 50 Ω/75 Ω/150 Ω cases, nearest supported values of 40 Ω/60 Ω/120 Ω are used.
4. Measured at 50% of V_{DDI}.
5. Supported terminations vary with the IO type regardless of V_{DDI} nominal voltage. Refer to Libero for available combinations.

Standard	STD	–1	Unit
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with V_{ID} ≥200 mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3[1]	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3[1]	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3[1]	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2[1]	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2[1]	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2[1]	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2[1]	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2[1]	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
FMAX 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
FMAX 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
FMAX 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
FMAX 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
FMAX 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
FMAX 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
FMAX 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
FMAX 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
FMAX 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
FMAX 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output F_{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance[1]	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V –1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V –1	Unit	Condition
Global clock F_{MAX}	F_{MAXG}	500	500	500	500	MHz	
Regional clock F_{MAX}	F_{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F_{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T_{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter[1]	Symbol	Min	Typ	Max	Unit
Secondary output clock frequency[2]	F_{OUTSF}	33.3		800	MHz
Input clock cycle-to-cycle jitter	F_{INJ}			200	ps
Output clock period cycle-to-cycle jitter (w/clean input)	$T_{OUTJITTERP}$			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T_{SKEW}			±200	ps
DLL lock time	T_{LOCK}	16		16K	Reference clock cycles
Minimum reset pulse width	T_{MRPW}	3			ns
Minimum input pulse width[3]	T_{MIPW}	20			ns
Minimum input clock pulse width high	T_{MPWH}	400			ps
Minimum input clock pulse width low	T_{MPWL}	400			ps
Delay step size	T_{DEL}	12.7	30	35	ps
Maximum delay block delay[4]	T_{DELMAX}	1.8		4.8	ns
Output clock duty cycle (with 50% duty cycle input)[5]	T_{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode)[5]	T_{DUTY50}	45		55	%

1. For all DLL modes.
2. Secondary output clock divided by four option.
3. On load, direction, move, hold, and update input signals.
4. 128 delay taps in one delay block.
5. Without duty cycle correction enabled.

7.2.4 RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front end information about emitters generated on-chip to support programming operations.

Table 39 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC_{2FREQ}		2		MHz
Accuracy	RC_{2FACC}	–4		4	%
Duty cycle	RC_{2DC}	46		54	%
Peak-to-peak output period jitter	RC_{2PJIT}		5	10	ns
Peak-to-peak output cycle-to-cycle jitter	RC_{2CJIT}		5	10	ns
Operating current (V_{DD25})	RC_{2IVPPA}			60	µA
Operating current (V_{DD})	RC_{2IVDD}			2.6	µA

Table 40 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC_{SCFREQ}		160		MHz
Accuracy	RC_{SCFACC}	–4		4	%
Duty cycle	RC_{SCDC}	47		52	%
Peak-to-peak output period jitter	RC_{SCPJIT}			600	ps
Peak-to-peak output cycle-to-cycle jitter	RC_{SCCJIT}			172	ps
Operating current (V_{DD25})	RC_{SCVPPA}			599	µA

Parameter	Symbol	Min	Typ	Max	Unit
Operating current (V_{DD18})	RC_{SCVPP}			0.1	µA
Operating current (V_{DD})	RC_{SCVDD}			60.7	µA

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate[1, 2, 3]	$F_{XCVRREFCLKMAX\ CASCADE}$	20		156	20		156	MHz
Reference clock rate at the PFD[4]	$F_{TXREFCLKPFD}$	20		156	20		156	MHz
Reference clock rate recommended at the PFD for Tx rates 10 Gbps and above[4]	$F_{TXREFCLKPFD10G}$	75		156	75		156	MHz
Tx reference clock phase noise requirements to meet jitter specifications (156 MHz clock at reference clock input)[5]	$F_{TXREFPN}$			–110			–110	dBc /Hz
Phase noise at 10 KHz	$F_{TXREFPN}$			–110			–110	dBc /Hz
Phase noise at 100 KHz	$F_{TXREFPN}$			–115			–115	dBc /Hz
Phase noise at 1 MHz	$F_{TXREFPN}$			–135			–135	dBc /Hz
Reference clock input rise time (10%–90%)	$T_{REFRISE}$		200	500		200	500	ps
Reference clock input fall time (90%–10%)	$T_{REFFALL}$		200	500		200	500	ps
Reference clock duty cycle	$T_{REFDUTY}$	40		60	40		60	%
Spread spectrum modulation spread[6]	Mod_Spread	0.1		3.1	0.1		3.1	%
Spread spectrum modulation frequency[7]	Mod_Freq	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	KHz

1. See the maximum reference clock rate allowed per input buffer standard.
2. The minimum value applies to this clock when used as an XCVR reference clock. It does not apply when used as a non-XCVR input buffer (DC input allowed).
3. Cascaded reference clock.
4. After reference clock input divider.
5. Required maximum phase noise is scaled based on actual $F_{TxRefClkPFD}$ value by 20 × log10 (TxRefClkPFD /156 MHz). It is assumed that the reference clock divider of 4 is used for these calculations to always meet the maximum PFD frequency specification.
6. Programmable capability for depth of down-spread or center-spread modulation.
7. Programmable modulation rate based on the modulation divider setting (1 to 63).

7.4.3 Transceiver Reference Clock I/O Standards

The following table describes the differential I/O standards supported as transceiver reference clocks.

Table 48 • Transceiver Differential Reference Clock I/O Standards

I/O Standard	Comment
LVDS25	For DC input levels, se e table Differential DC Input and Output Levels.
HCSL25 (for PCIe)	

Note: The transceiver reference clock differential receiver supports V_{CM} common mode.

7.4.4 Transceiver Interface Performance

The following table describes the single-ended I/O standards supported as transceiver reference clocks.

Table 49 • Transceiver Single-Ended Reference Clock I/O Standards

I/O Standard	Comment
LVCMOS25	For DC input levels, see table DC Input and Output Levels.

7.4.5 Transmitter Performance

The following tables describe performance of the transmitter.

Table 50 • Transceiver Reference Clock Input Termination

Parameter	Symbol	Min	Typ	Max	Unit
Single-ended termination	RefTerm		50		Ω
Single-ended termination	RefTerm		75		Ω
Single-ended termination	RefTerm		150		Ω
Differential termination	RefDiffTerm		115[1]		Ω
Power-up termination			>50K		Ω

1. Measured at VCM= 1.2 V and VID= 350 mV.

Note: All pull-ups are disabled at power-up to allow hot plug capability.

Table 51 • PolarFire Transceiver User Interface Clocks

Parameter	Modes [1]	STD Min	STD Max	–1 Min	–1 Max	Unit
Transceiver TX_CLK range (non-deterministic PCS mode with global or regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		325		325	MHz
	40-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		260		320	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		165		160	MHz
	80-bit, max data rate = 10.3125 Gbps(–STD) / 12.7 Gbps (–1)[1]		130		130	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz
	8-bit, max data rate = 1.6 Gbps		200		200	MHz

Parameter	Symbol	Min	Typ	Max	Unit	Condition
		0.41			UI	>3.2–8.5 Gbps[5]
		0.41			UI	>1.6 to 3.2 Gbps[5]
		0.41			UI	>0.8 to 1.6 Gbps [5]
		0.41			UI	250 to 800 Mpbs [5]
Total jitter tolerance with stressed eye	$T_{TJTOLSE}$	0.65			UI	3.125 Gbps[5]
		0.65			UI	6.25 Gbps[6]
		0.7			UI	10.3125 Gbps[6]
					UI	12.7 Gbps[6, 10]
Sinusoidal jitter tolerance with stressed eye	$T_{SJTOLSE}$	0.1			UI	3.125 Gbps[5]
		0.05			UI	6.25 Gbps[6]
		0.05			UI	10.3125 Gbps[6]
					UI	12.7 Gbps[6, 10]
CTLE DC gain (all stages, max settings)				10	dB	
CTLE AC gain (all stages, max settings)				16	dB	
DFE AC gain (per 5 stages, max settings)				7.5	dB	

1. Valid at 3.2 Gbps and below.
2. Data vs. Rx reference clock frequency.
3. Achieves compliance with PCIe electrical idle detection.
4. Achieves compliance with SATA OOB specification.
5. Rx jitter values based on bit error ratio (BER) of 10–12, AC coupled input with 400 mV V_{ID}, all stages of Rx CTLE enabled, DFE disabled, 80 MHz sinusoidal jitter injected to Rx data.
6. Rx jitter values based on bit error ratio (BER) of 10–12, AC coupled input with 400 mV V_{ID}, all stages of Rx CTLE enabled, DFE enabled, 80 MHz sinusoidal jitter injected to Rx data.
7. For PCIe: Low Threshold Setting = 1, High Threshold Setting = 2.
8. For SATA: Low Threshold Setting = 2, High Threshold Setting = 3.
9. Loss of signal detection is valid for input signals that transition at a density ≥1 Gbps for PRBS7 data or 6 Gbps for PRBS31 data.
10. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.5 Transceiver Protocol Characteristics

The following section describes transceiver protocol characteristics.

7.5.1 PCI Express

The following tables describe the PCI express.

Table 54 • PCI Express Gen1

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	2.5 Gbps		0.25	UI
Receiver jitter tolerance	2.5 Gbps	0.4		UI

Note: With add-in card, as specified in PCI Express CEM Rev 2.0.

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable)[1]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53[1]	s
	MPF300T, TL, TS, TLS	90[1]	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37[2]	s
	MPF300T, TL, TS, TLS	55[2]	s
	MPF500T, TL, TS, TLS		s

1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours ove r the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Authenticated text read		113.25	114.02	118.5	µs	
Authenticated and decrypted text read		159.59	160.53	166.5	µs	

Notes:

- Page size= 252 bytes (non-authenticated), 236 bytes (authenticated).
- Only page reads and writes allowed.
- T_{PUF_OVHD} is an additional time that occurs on the first R/W, after cold or warm boot, to sNVM using authenticated or authenticated and encrypted text.

7.6.10 Secure NVM Programming Cycles

The following table describes secure NVM programming cycles.

Table 86 • sNVM Programming Cycles vs. Retention Characteristics

Programming Temperature	Programming Cycles per Page, Max	Programming Cycles per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 bytes. Block size = 56 KBytes.

7.7 System Services

This section describes system switching and throughput characteristics.

7.7.1 System Services Throughput Characteristics

The following table describes system services throughput characteristics.

Table 87 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Serial number	T_{Serial}	00H	65	67	µs	
User code	T_{User}	01H	0.8	1.05	µs	
Design information	T_{Design}	02H	2.4	2.7	µs	
Device certificate	T_{Cert}	03H	255	271	ms	
Read digests	T_{digest_read}	04H	201	215	µs	
Query security locks	T_{sec_Query}	05H	15	17	µs	
Read debug information	T_{Rd_debug}	06H	34	38	µs	
Reserved		07H–0FH				
Secure NVM write plain text	$T_{SNVM\_Wr\_Plain}$	10H				Note 1
Secure NVM write authenticated plain text	$T_{SNVM\_Wr\_Auth}$	11H				Note 1
Secure NVM write authenticated cipher text	$T_{SNVM\_Wr\_Cipher}$	12H				Note 1
Reserved		13H–17H				

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Secure NVM read	T_{SNVM_Rd}	18H				Note 1
Digital signature service raw	T_{SIG_RAW}	19H	174	187	ms	
Digital signature service DER	T_{SIG_DER}	1AH	174	187	ms	
Reserved		1BH–1FH				
PUF emulation	$T_{Challenge}$	20H	1.8	2.0	ms	
Nonce service	T_{Nonce}	21H	1.2	1.4	ms	
Bitstream authentication	TBIT_AUTH	22H				Note 4
IAP Image authentication	TIAP_AUTH	23H				Note 4
Reserved		26H–3FH				
In application programming by index	$T_{IAP\_Prg\_Index}$	42H				Note 2
In application programming by SPI address	$T_{IAP\_Prg\_Addr}$	43H				Note 2
In application verify by index	TIAP_Ver_Index	44H				Note 5
In application verify by SPI address	TIAP_Ver_Addr	45H				Note 5
Auto update	$T_{AutoUpdate}$	46H				Note 2
Digest check	T_{digest_chk}	47H				Note 3

1. See sNVM Read/Write Characteristics (see page 58).
2. See SPI Master Programming Time (see page 52).
3. See Digest Times (see page 54).
4. See Authentication Services Time (see page 58).
5. See Verify Services Time (see page 58).
6. Throughputs described are measured from SS_REQ assertion to BUSY de-assertion.

7.8 Fabric Macros

This section describes switching characteristics of UJTAG, UJTAG_SEC, USPI, system controller, and temper detectors and dynamic reconfiguration details.

7.8.1 UJTAG Switching Characteristics

The following section describes characteristics of UJTAG switching.

Table 88 • UJTAG Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F_{TCK}			25	MHz	

Table 107 • SPI Master Mode (PolarFire Master) During Device Initialization

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{MSCK}			40	MHz	

Table 108 • SPI Slave Mode (PolarFire Slave)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{SSCK}			80	MHz	

7.10.3 SmartDebug Probe Switching Characteristics

The following table describes characteristics of SmartDebug probe switching.

Table 109 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V – 1	Unit
Maximum frequency of probe signal	F_{MAX}	100	100	100	100	MHz
Minimum delay of probe signal	T_{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T_{Max_delay}	13	12	13	12	ns

7.10.4 DEVRST_N Switching Characteristics

The following table describes characteristics of DEVRST_N switching.

Table 110 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR_{RAMP}		10		µs	It must be a normal clean digital signal, with typical rise and fall times
DEVRST_N assert time	DR_{ASSERT}	1			µs	The minimum time for DEVRST_N assertion to be recognized
DEVRST_N de-assert time	$DR_{DEASSERT}$	2.75			ms	The minimum time DEVRST_N needs to be de-asserted before assertion

7.10.5 FF_EXIT Switching Characteristics

The following table describes characteristics of FF_EXIT switching.

Table 111 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF_{RAMP}		10		µs	
Minimum FF_EXIT_N assert time	FF_{ASSERT}	1			µs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	$FF_{DEASSERT}$	170			µs	The minimum time FF_EXIT_N needs to be de-asserted before assertion

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